

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-9. (Canceled)

10. (Previously presented) A junction field-effect transistor comprising:  
a first conductivity type first semiconductor layer having a substantially flat cross-sectional shape and having a channel region,  
a buffer layer of a second conductivity type formed on the channel region in the first conductivity type first semiconductor layer, the buffer layer having a substantially flat cross-sectional shape , and  
a second conductivity type doped region extending into the first conductivity type first semiconductor layer to a top surface of the buffer layer, but not extending through the buffer layer,  
wherein a second conductivity type carrier concentration in the buffer layer is lower than a first conductivity type carrier concentration in the first conductivity type first semiconductor layer.

11. (Previously presented) The junction field-effect transistor according to claim 10 wherein the first conductivity type first semiconductor layer is composed of silicon carbide.

12. (Previously presented) The junction field-effect transistor according to claim 10 further comprising another second conductivity type doped region under the channel region.

13. (Previously presented) The junction field-effect transistor according to claim 10 further comprising:

another buffer layer of the first conductivity type under the channel region, and

another second conductivity type doped region that reaches the other buffer layer and is in a first conductivity type second semiconductor layer under the other buffer layer,

wherein a first conductivity type carrier concentration in the other buffer layer is lower than a first conductivity type carrier concentration in the first conductivity type first semiconductor layer.

14. (Previously Presented) The junction field-effect transistor according to claim 13 where the first conductivity type carrier concentration in the other buffer layer is not more than one tenth of the first conductivity type carrier concentration in the first conductivity type first semiconductor layer.

15. (Previously presented) The junction field-effect transistor according to claim 10 further comprising a semiconductor substrate composed of n-type silicon carbide,

wherein the first conductivity type first semiconductor layer is formed on one main surface of the semiconductor substrate.

16. (Previously presented) The junction field-effect transistor according to claim 15 further comprising:

a gate electrode on the surface of the second conductivity type doped region,

an electrode, either a source electrode or a drain electrode, on the surface of the first conductivity type first semiconductor layer, and

another electrode, either a drain electrode or a source electrode, on another main surface of the semiconductor substrate.

17. (Previously presented) The junction field-effect transistor according to claim 15 further comprising:

a gate electrode on the surface of the second conductivity type doped region, and

a source electrode and a drain electrode on the surface of the first conductivity type first semiconductor layer.

18. (Canceled)

19. (Previously Presented) The junction field-effect transistor according to claim 10 wherein the second conductivity type doped region does not extend into the buffer layer.